AMENDMENTS TO THE CLAIMS:

Please cancel claims 99, 102, and 104, without prejudice or disclaimer of the subject matter thereof, amend claims 83, 92, 100, 101, 103, 109, 112, 114, 115, 121, 123, and 124, and add new claims 125-137 as follows.

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Withdrawn) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

contacts for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion region; and

an elongate current divider extending between the channel and a region of the contacts.

2. (Withdrawn) The protection device of claim 1, further including a polysilicon gate overlying the channel.

3. (Withdrawn) The protection device of claim 1, further including a stripe of field oxide overlying the channel.

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4. (Withdrawn) The protection device of claim 1, wherein the substrate comprises a well region.

5. (Withdrawn) The protection device of claim 1, wherein the substrate comprises a semiconductor layer over an insulator layer.

6. (Withdrawn) The protection device of claim 1, wherein the current divider has first and second ends, the first end being connected to the channel.

7. (Withdrawn) The protection device of claim 1, wherein the current divider has first and second ends, the first end being spaced from the channel.

8. (Withdrawn) The protection device of claim 1, wherein at least a portion of the current divider is disposed at an acute angle relative to the channel.

9. (Withdrawn) The protection device of claim 1, wherein the current divider is disposed substantially perpendicularly to the channel.

10. (Withdrawn) The protection device of any one of claims 1 - 9, wherein the current divider is formed of one of polysilicon, field oxide, and a structure of polysilicon at least partially overlapping a field oxide.

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11. (Withdrawn) The protection device of any one of claims 1 - 9, wherein the current divider comprises a field oxide layer overlayed by a polysilicon layer, a periphery of the polysilicon layer extending beyond an edge of the field oxide layer.

12. (Withdrawn) The protection device of claim 1, wherein the substrate comprises a silicon-on-insulator structure.

13. (Withdrawn) The protection device of claim 1, wherein the current divider comprises a layer of polysilicon formed over a layer of thin oxide.

14. (Withdrawn) The protection device of claim 13, wherein the substrate comprises a silicon-on-insulator structure.

15. (Withdrawn) The protection device of claim 1, further including a conductive gate overlying the channel;

wherein the current divider is formed of field oxide, one end portion of the current divider partially extending underneath the gate.

16. (Withdrawn) The protection device of claim 15, wherein the end portion of the current divider is narrower than another portion of the current divider.

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17. (Withdrawn) The protection device of claim 1, further including a conductive gate overlying the channel; and

the current divider being formed of field oxide.

18. (Withdrawn) The protection device of claim 17, wherein an end of the current divider nearest the gate is spaced therefrom.

19. (Withdrawn) The protection device of claim 18, further including a conductive extension member extending from the gate and overlying the near end of the current divider.

20. (Withdrawn) The protection device of claim 15, further including a conductive extension member extending from the gate and overlying at least part of the end portion of the current divider not partially extending underneath the gate.

21. (Withdrawn) The protection device of claim 1, further including a polysilicon gate formed over a thin oxide and overlying the channel; and

wherein the current divider comprises a layer of polysilicon formed over a thin oxide, the current divider extending from and contiguous with the gate.

22. (Withdrawn) The protection device of claim 21, wherein the current divider is substantially perpendicular to the gate.

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23. (Withdrawn) The protection device of claim 1, further including a stripe of field oxide overlying the channel, the current divider being spaced from the field oxide stripe.

24. (Withdrawn) The protection device of claim 23, wherein the current divider is formed of field oxide.

25. (Withdrawn) The protection device of claim 24, wherein the current divider includes a layer of polysilicon at least partially overlapping the field oxide.

26. (Withdrawn) The protection device of claim 23, wherein the current divider comprises a layer of polysilicon formed over a thin oxide.

27. (Withdrawn) The protection device of claim 1, further including a stripe of field oxide overlying the channel;

wherein the current divider is formed of field oxide.

28. (Withdrawn) The protection device of claim 27, wherein the current divider extends from and is contiguous with the field oxide stripe.

29. (Withdrawn) The protection device of claim 28, wherein the current divider is substantially perpendicular to the field oxide stripe.

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30. (Withdrawn) The protection device of any one of claims 15-21, further including a plurality of the current dividers substantially parallel to each other.

31. (Withdrawn) The protection device of claim 30, wherein each of the plurality of current dividers is substantially perpendicular to the gate.

32. (Withdrawn) The protection device of any one of claims 23-28, further including a plurality of the current dividers substantially parallel to each other.

33. (Withdrawn) The protection device of claim 32, wherein each of the plurality of current dividers is substantially perpendicular to the stripe of field oxide.

34. (Withdrawn) The protection device of claim 11 further including an electrical connection to the polysilicon layer.

35. (Withdrawn) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in a spaced relationship to the first diffusion region;

a third diffusion region formed in the substrate between and spaced from the first and second diffusion regions;

a first gate overlying a region between the first and third diffusion regions;

a second gate overlying a region between the second and third diffusion regions;

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contacts for making a conductive connection to the third diffusion region;

a first elongate current divider extending between the first gate and a region of the contacts; and

a second elongate current divider extending between the second gate and the region of the contacts.

36. (Withdrawn) The protection device of claim 35, wherein the substrate comprises a well region.

37. (Withdrawn) The protection device of claim 35, wherein the substrate comprises a semiconductor layer over an insulator layer.

38. (Withdrawn) The protection device of claim 35, wherein the first current divider has first and second ends, the first end being connected to the first gate; and

the second current divider having first and second ends, the first end being connected to the second gate.

39. (Withdrawn) The protection device of claim 35, wherein the first current divider has first and second ends, the first end being spaced from the first gate; and

the second current divider having first and second ends, the first end being spaced from the second gate.

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40. (Withdrawn) The protection device of claim 35, wherein the first current divider is disposed at an acute angle relative to the first gate; and

the second current divider is disposed at the acute angle relative to the second gate such that the second current divider is disposed substantially symmetrically relative to the first current divider.

41. (Withdrawn) The protection device of claim 40, wherein the first current divider has first and second ends, the first end being connected to the first gate; and the second current divider having first and second ends, the first end being connected to the second gate.

42. (Withdrawn) The protection device of claim 40, wherein the first current divider has first and second ends, the first end being spaced from the first gate; and

the second current divider having first and second ends, the first end being spaced from the second gate.

43. (Withdrawn) The protection device of claim 35, wherein the first and second current dividers join in the region of the contacts to form a single current divider structure.

44. (Withdrawn) The protection device of claim 43, wherein an end of the first current divider remote from the second current divider is connected to the first gate; and

an end of the second current divider remote from the first current divider is connected to the second gate.

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45. (Withdrawn) The protection device of claim 43, wherein an end of the first current divider remote from the second current divider is spaced from the first gate; and

an end of the second current divider remote from the first current divider is spaced from the second gate.

46. (Withdrawn) The protection device of claim 40, wherein the first and second current dividers are each formed of polysilicon;

the protection device further including a third current divider formed of field oxide and connected between the second ends of the first and second current dividers, the third current divider being positioned between adjacent contacts in the region of the contacts.

47. (Withdrawn) The protection device of claim 35, wherein the first current divider is disposed substantially perpendicularly to the first gate; and

the second current divider is disposed substantially perpendicularly to the second gate.

48. (Withdrawn) The protection device of claim 47, wherein the first current divider has first and second ends, the first end being connected to the first gate; and

the second current divider having first and second ends, the first end being connected to the second gate.

49. (Withdrawn) The protection device of claim 47, wherein the first current divider has first and second ends, the first end being spaced from the first gate; and

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the second current divider having first and second ends, the first end being spaced from the second gate.

50. (Withdrawn) The protection device of claim 47, wherein the first and second current dividers join in the region of the contacts to form a single current divider structure.

51. (Withdrawn) The protection device of claim 50, wherein an end of the first current divider remote from the second current divider is connected to the first gate; and

an end of the second current divider remote from the first current divider is connected to the second gate.

52. (Withdrawn) The protection device of claim 50, wherein an end of the first current divider remote from the second current divider is spaced from the first gate; and

an end of the second current divider remote from the first current divider is spaced from the second gate.

53. (Withdrawn) The protection device of any one of claims 35 - 45 or 47 - 52, wherein the first and second current dividers are both formed of one of polysilicon, field oxide, and a structure of polysilicon partially overlapping field oxide.

54. (Withdrawn) The protection device of any one of claims 35 - 45 or 47 - 52, wherein at least one of the first and second current dividers comprises a field oxide layer.

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55. (Withdrawn) The protection device of any one of claims 54, wherein a periphery of the polysilicon layer extends beyond an edge of the field oxide layer.

56. (Withdrawn) The protection device of claim 47, wherein the first and second current dividers are each formed of polysilicon;

the protection device further including a third current divider formed of field oxide and connected between the second ends of the first and second current dividers, the third current divider being positioned between adjacent contacts in the region of the contacts.

57. (Withdrawn) The protection device of claim 43, wherein the single current divider structures are each formed of field oxide and extend beneath and beyond the first and second gates.

58. (Withdrawn) The protection device of claim 43, wherein the single current divider structures are each formed of field oxide, are substantially parallel to each other, and are skewed relative to the first and second gates.

59. (Withdrawn) The protection device of claim 43, wherein the single current divider structures are each formed of field oxide, are substantially parallel to each other, respective ends of each of the current divider structures being spaced from the first and second gates, and the single current divider structures being substantially perpendicular to the first and second gates.

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60. (Withdrawn) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

contacts for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion region;

a first elongate current divider extending between the channel and a region of the contacts; and

a second elongate current divider adjacent to the first divider and extending between the channel and a region of the contacts.

61. (Withdrawn) The protection device of claim 60, further including a polysilicon gate overlying the channel.

62. (Withdrawn) The protection device of claim 60, further including a stripe of field oxide overlying the channel.

63. (Withdrawn) The protection device of claim 60, wherein the substrate comprises a well region.

64. (Withdrawn) The protection device of claim 60, wherein the substrate comprises a semiconductor layer over an insulator layer.

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65. (Withdrawn) The protection device of claim 60, wherein each of the first and second current dividers has first and second ends, the first end being connected to the channel.

66. (Withdrawn) The protection device of claim 60, wherein each of the first and second current dividers has first and second ends, the first end being spaced from the channel.

67. (Withdrawn) The protection device of claim 60, wherein at least a portion of each of the first and second current dividers is disposed at an acute angle relative to the channel.

68. (Withdrawn) The protection device of claim 60, wherein each of the first and second current dividers is disposed substantially perpendicularly to the channel.

69. (Withdrawn) The protection device of any one of claims 60 - 68, wherein each of the first and second current dividers is formed of one of the polysilicon, field oxide, and a structure of polysilicon partially overlapping field oxide.

70. (Withdrawn) The protection device of any one of claims 60 - 68, wherein the current divider comprises a field oxide layer overlayed by a polysilicon layer, a periphery of the polysilicon layer extending beyond an edge of the field oxide layer.

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71. (Withdrawn) The protection device of any one of claims 70, wherein the current divider comprises a field oxide layer overlayed by a polysilicon layer, a periphery of the polysilicon layer extending beyond an edge of the field oxide layer.

72. (Withdrawn) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in a spaced relationship to the first diffusion region;

a third diffusion region formed in the substrate between and spaced from the first and second diffusion regions;

a first gate overlying a region between the first and third diffusion regions;

a second gate overlying a region between the second and third diffusion regions;

contacts for making a conductive connection to the third diffusion region;

a plurality of adjacent first elongate current dividers extending between the first gate and a region of the contacts; and

a plurality of adjacent second elongate current dividers extending between the second gate and the region of the contacts.

73. (Withdrawn) The protection device of claim 72, wherein each of the first current dividers has first and second ends, the first ends being connected to the first gate; and

each of the second current dividers having first and second ends, the first ends being connected to the second gate.

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74. (Withdrawn) The protection device of claim 72, wherein each of the first current dividers has first and second ends, the first end being spaced from the first gate; and

each of the second current dividers having first and second ends, the first ends being spaced from the second gate.

75. (Withdrawn) The protection device of claim 72, wherein each of the first current dividers is disposed at an acute angle relative to the first gate; and

each of the second current dividers is disposed at the acute angle relative to the second gate such that each of the second current dividers is disposed substantially symmetrically relative to a corresponding one of the first current dividers.

76. (Withdrawn) The protection device of claim 75, wherein each of the first current dividers has first and second ends, the first ends being connected to the first gate; and

each of the second current dividers having first and second ends, the first ends being connected to the second gate.

77. (Withdrawn) The protection device of claim 75, wherein each of the first current dividers has first and second ends, the first ends being spaced from the first gate; and

each of the second current dividers having first and second ends, the first ends being spaced from the second gate.

78. (Withdrawn) The protection device of claim 72, wherein each of the first current dividers joins a corresponding one of the second current dividers in the region of the contacts to

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form a plurality of adjacent single current divider structures respectively extending between the first and second gates.

79. (Withdrawn) The protection device of claim 78, wherein an end of each of the first current dividers remote from the corresponding second current divider is connected to the first gate; and

an end of the second current divider remote from the corresponding first current divider is connected to the second gate.

80. (Withdrawn) The protection device of claim 78, wherein an end of each of the first current dividers remote from the corresponding second current divider is spaced from the first gate; and

an end of each of the second current dividers remote from the corresponding first current divider is spaced from the second gate.

81. (Withdrawn) An electrostatic discharge (ESD) protection device formed on a first type semiconductor substrate, comprising:

a gate having a continuous structure located over the first type semiconductor substrate;

a common source region in the first type semiconductor substrate on one side of the gate;

a plurality of drain regions in the first type semiconductor substrate located on an opposite side of the gate, wherein the plurality of drain regions are isolated from each other and adjacent to the gate;

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a plurality of contacts distributed over the common source region and the plurality of drain regions;

a first metal bus over the common source region;

a plurality of first contacts connecting the common source region to the first metal bus;

a second metal bus over the plurality of drain regions;

a plurality of second contacts connecting the plurality of drain regions to the second metal bus.

82. (Withdrawn) A semiconductor field-effect transistor device for electrostatic discharge protection of a semiconductor integrated circuit device, comprising:

a substrate;

a gate having an extended stripe-shaped structure formed on the substrate;

a drain region formed in the substrate on a first side of the gate;

a source region formed in the substrate on a second side of the gate;

a plurality of parallel-aligned field oxide islands formed over a surface of the substrate, the plurality of field oxide islands originating from the first side of the gate and extending underneath the gate without extending to the second side of the gate, wherein the plurality of field oxide islands divide part of the drain region into an array of parallel current paths and do not divide the source diffusion region.

83. (Currently Amended) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

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a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

at least one contact for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions; and

a plurality of current divider segments ~~randomly~~ distributed within the first diffusion region,

wherein said segments include first and second segments formed of different constructions.

84. (Previously Presented) The device of claim 96, wherein the different shapes are selected from a square, a circle, a cross shape, a T shape, a V shape, a U shape, and an L shape.

85. (Previously Presented) The device of claim 96, wherein the different shapes differ from each other with respect to at least one of length, width, size, and area.

86. (Original) The device of claim 83, wherein the largest dimension of each segment is less than or equal to substantially six times a length of the channel.

87. (Original) The device of claim 83, wherein the plurality of segments are formed of polysilicon segments, field oxide segments, or a combination of polysilicon and field oxide segments.

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88. (Previously Presented) The device of claim 83, wherein

the plurality of segments includes a first row of segments;

each one of the first row of segments has a center-of-area, the respective centers-of-area are not aligned in a straight line.

89. – 91. (Canceled)

92. (Currently Amended) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

contacts for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions; and

a plurality of current divider segments formed within the first diffusion region and being randomly distributed therein,

wherein at least one of the plurality of current divider segments is completely surrounded by the first diffusion region and formed of a construction different from at least one other of the plurality of current divider segments.

93. (Withdrawn) A method for forming an electrostatic discharge protection device, comprising the steps of:

forming a substrate;

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forming a first diffusion region formed in the substrate;

forming a second diffusion region in the substrate adjacent to and spaced from the first diffusion region;

forming contacts for making a conductive connection to the first diffusion region;

forming a channel in a third region between the first and second diffusion region; and

forming an elongate current divider extending between the channel and a region of the contacts.

94. (Withdrawn) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

contacts for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions;

a plurality of current divider segments formed within the first diffusion region and being one of evenly and unevenly distributed therein, at least one of the segments comprising a field oxide layer overlayed by a polysilicon layer; and

a contact formed on the polysilicon layer.

95. (Withdrawn) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

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a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

a channel formed in a third region between the first and second diffusion regions;

at least one current divider segment formed within the first diffusion region, the current divider segment comprising a field oxide layer overlapped by a polysilicon layer; and

a periphery of the polysilicon layer extending beyond an edge of the field oxide layer.

96. (Previously Presented) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

a contact for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions;

a plurality of current divider segments formed within and completely surrounded by the first diffusion region including first and second segments formed in at least one of different shapes, different sizes, and different orientations with respect to each other.

97. – 99. (Canceled)

100. (Currently Amended) The device of claim ~~99~~ 83, wherein said segments include the first segment formed of a polysilicon layer or a field oxide layer; and the second segment formed of a polysilicon layer or a field oxide layer.

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101. (Currently Amended) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced apart from the first diffusion region;

a contact for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions; and

a plurality of current divider segments formed within and completely surrounded by the first diffusion region,

wherein said segments include a first segment adjacent to a second segment and spaced apart from the second segment by a first gap in a first direction ~~from an adjacent second segment~~;

said segments further include a third segment adjacent to the second segment and spaced apart from the second segment by a second gap in the first direction ~~from an adjacent fourth segment~~; and

said first gap being larger than the second gap.

102. (Canceled)

103. (Currently Amended) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

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a second diffusion region formed in the substrate adjacent to and spaced apart from the first diffusion region;

a contact for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions; and

a plurality of current divider segments formed within and completely surrounded by the first diffusion region,

wherein said segments include a first segment having a first center-of-area, adjacent to a second segment having a second center-of-area, and being spaced apart from ~~an~~ the ~~adjacent~~ second segment ~~having a second center-of-area~~;

a third segment having a third center-of-area, adjacent to the second segment, and being spaced apart from the second segment ~~an adjacent fourth segment having a fourth center-of-area~~;

a first distance in a first direction between the first and second centers-of-area;

a second distance in the first direction between the third and ~~fourth~~ second centers-of-area; and

the first distance being larger than the second distance.

104. (Canceled)

105. (Previously Presented) The device of claim 83, further including a dielectric layer formed over the channel.

106. (Previously Presented) The device of claim 105, further including a conductive element formed over the dielectric layer.

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107. (Previously Presented) The device of claim 106, wherein

the conductive element is a polysilicon gate element; and

the dielectric layer is an oxide layer.

108. (Previously Presented) The device of claim 83, wherein at least one of the segments is positioned between the at least one contact and the channel.

109. (Currently Amended) The device of claim 83, wherein [the segments include at least a] the first segment is formed of a dielectric layer.

110. (Previously Presented) The device of claim 109, wherein the dielectric layer is a field oxide layer.

111. (Previously Presented) The device of claim 110, wherein the field oxide layer is formed by one of a LOCOS process and a trench isolation process.

112. (Currently Amended) The device of claim 83, wherein ~~the segments include at least a~~ the first segment is formed of a ~~polysilicon~~ conductive layer ~~or a field oxide layer~~ over a dielectric layer.

113. (Previously Presented) The device of claim 112, wherein

the conductive layer is a polysilicon layer; and

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the dielectric layer is a ~~gate~~ oxide layer.

114. (Currently Amended) The device of claim 83, wherein at least one of said segments has a ~~shape~~ construction selected from a square, a circle, a cross shape, a T shape, a V shape, a U shape, and an L shape.

115. (Currently Amended) The device of claim 83 wherein at least one of said segments has a first portion in a ~~shape~~ construction selected from a square, a circle, a cross shape, a T shape, a V shape, a U shape, and L shape.

116. (Previously Presented) The device of claim 83, wherein

each one of said segments has a center-of-area; and

at least a first center-of-area being not aligned with a second and a third centers-of-area.

117. – 120. (Canceled)

121. (Currently Amended) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

a contact region for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions; and

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a plurality of current divider segments formed within the first diffusion region between said contact region and the channel and ~~each of~~ a center of the current divider segments formed within the first diffusion region being closer to the channel than to the contact region.

122. (Previously Presented) The device of claim 121, wherein the contract region includes a plurality of contacts.

123. (Currently Amended) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

at least one contact for making a conductive connection to the first diffusion region;

a channel region formed in a third region between the first and second diffusion regions;

a first current divider segment formed within the first diffusion region having a first portion, a longitudinal axis of the first portion being oriented at an angle ~~not~~ neither parallel with nor perpendicular to a longitudinal direction of the channel region.

124. (Currently Amended) The device of claim 123, wherein the first current divider segment further having a second portion, a longitudinal axis of the second portion being oriented at a second angle to the first portion.

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125. (New) The device of claim 83, wherein the plurality of current divider segments are randomly distributed within the first diffusion region.

126. (New) The device of claim 121, wherein said center is an area center.

127. (New) The device of claim 121, wherein said center is a weight center.

128. (New) The device of claim 83, wherein at least one current divider segment of the plurality of current divider segments includes an oxide spacer formed on sidewalls of the at least one current divider segment.

129. (New) The device of claim 92, wherein at least one current divider segment of the plurality of current divider segments includes an oxide spacer formed on sidewalls of the at least one current divider segment.

130. (New) The device of claim 96, wherein at least one current divider segment of the plurality of current divider segments includes an oxide spacer formed on sidewalls of the at least one current divider segment.

131. (New) The device of claim 101, wherein at least one current divider segment of the plurality of current divider segments includes an oxide spacer formed on sidewalls of the at least one current divider segment.

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132. (New) The device of claim 103, wherein at least one current divider segment of the plurality of current divider segments includes an oxide spacer formed on sidewalls of the at least one current divider segment.

133. (New) The device of claim 121, wherein at least one current divider segment of the plurality of current divider segments includes an oxide spacer formed on sidewalls of the at least one current divider segment.

134. (New) The device of claim 123, wherein the first current divider segment includes an oxide spacer formed on sidewalls of the first current divider segment.

135. (New) The device as in any one of claims 83, 92, 96, 101, 103, 121, or 123, wherein

the first diffusion region includes a heavily doped region, and

at least one current divider segment is characterized by an implant blocking region completely surrounded by the heavily doped region.

136. (New) The device of claim 121, wherein the first diffusion region is a drain region.

137. (New) The device of claim 121, wherein the first diffusion region is a collector region.

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